L Numb r	Hits	Search T xt	DB	Time stamp
l l	4	"6504585"	USPAT;	2003/02/10
ļ		i	US-PGPUB;	08:57
i i			EPO; JPO;	
			DERWENT;	1
			IBM_TDB	
2	1	"6504585" and video	USPAT;	2003/02/10
			US-PGPUB;	08:57
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
3	4	"6249325"	USPAT;	2003/02/10
			US-PGPUB;	08:57
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
4	3	"6249325" and video	USPAT;	2003/02/10
			US-PGPUB:	08:57
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	25	((substrate near5 transparent) and (gate and	USPAT;	2003/02/04
	20	drain) and (tft or (thin near film near	US-PGPUB;	16:23
		transistor)) and pixel and electrode and	EPO; JPO;	10.23
		source and counter).clm.	DERWENT;	
		source and counter).cim.		
	20		IBM_TDB	2002/02/05
-	20	(((substrate near5 transparent) and (gate	USPAT;	2003/02/05
		and drain) and (tft or (thin near film near	US-PGPUB;	10:43
		transistor)) and pixel and electrode and	EPO; JPO;	
		source and counter).clm.) and (source near	DERWENT;	
		electrode).clm.	IBM_TDB	
•	42	((pixel near electrode) and (counter near	USPAT;	2003/02/05
		electrode) and (source near electrode) and	US-PGPUB;	10:48
	İ	substrate and transparent).clm.	EPO; JPO;	
	İ		DERWENT;	
			IBM_TDB	
	31	(((pixel near electrode) and (counter near	USPAT;	2003/02/05
	İ	electrode) and (source near electrode) and	US-PGPUB;	10:51
1		substrate and transparent).clm.) and (tft or	EPO; JPO;	
		(thin near film near transistor)).clm.	DERWENT;	
	]		IBM_TDB	
	29	((((pixel near electrode) and (counter near	USPAT;	2003/02/05
		electrode) and (source near electrode) and	US-PGPUB;	10:52
		substrate and transparent).clm.) and (tft or	EPO; JPO;	
		(thin near film near transistor)).clm.) and	DERWENT;	
		(gate and drain).clm.	IBM_TDB	
i	1	((((((pixel near electrode) and (counter near	USPAT;	2003/02/05
		I ctr de) and (s urce near electrode) and	US-PGPUB;	10:53
		substrate and transpar nt).clm.) and (tft r	EPO; JPO;	
		(thin n ar film near transist r)).clm.) and	DERWENT;	
		(gat and drain).clm.) and (matrix or	IBM_TDB	
		array).clm.) and c nt ur.clm.		

•	15	(((((pixel near ! trode) and (c unt r near	USPAT;	2003/02/05
		electr de) and (s urce near el ctr de) and	US-PGPUB;	10:54
		substrate and transparent).clm.) and (tft or	EPO; JPO;	
	1	(thin n ar film n ar transistor)).clm.) and	DERWENT;	
		(gat and drain).clm.) and (matrix or	IBM_TDB	
	i	array).clm.		
	1	((((((pixel near electrode) and (counter near	USPAT;	2003/02/05
		electrode) and (source near electrode) and	US-PGPUB;	10:55
	i i	substrate and transparent).clm.) and (tft or	EPO; JPO;	
		(thin near film near transistor)).clm.) and	DERWENT;	
		(gate and drain).clm.) and (matrix or	IBM_TDB	
		array).clm.) and contour		
	2	((substrate near10 transparent) and (lcd or	USPAT;	2003/02/05
		(liquid near crystal)) and (gate near line) and	US-PGPUB;	10:58
		(drain near line) and (tft or (thin near film	EPO; JPO;	
		near transistor)) and (pixel near electrode)	DERWENT;	
		and (counter near electrode) and edge).clm.	IBM_TDB	
	_		USPAT;	2003/02/05
	7	((substrate near10 transparent) and (lcd or	US-PGPUB;	11:02
		(liquid near crystal)) and (gate near line) and	EPO; JPO;	
	•	(drain near line) and (tft or (thin near film		
		near transistor)) and (pixel near electrode)	DERWENT;	
		and (counter near electrode)).clm.	IBM_TDB	2003/02/05
	146	((substrate near10 transparent) and (lcd or	USPAT;	
		(liquid near crystal)) and (gate near line) and	US-PGPUB;	11:04
		(drain near line) and (tft or (thin near film	EPO; JPO;	
		near transistor)) and (pixel near electrode)	DERWENT;	
		and (counter near electrode))	IBM_TDB	
	3	(((substrate near10 transparent) and (lcd or	USPAT;	2003/02/05
	1	(liquid near crystal)) and (gate near line) and	US-PGPUB;	11:08
		(drain near line) and (tft or (thin near film	EPO; JPO;	
		near transistor)) and (pixel near electrode)	DERWENT;	1
	1	and (counter near electrode))) and	IBM_TDB	
		(photoconductive or (photo near		
		conductive))		
	6	(((substrate near10 transparent) and (lcd or	USPAT;	2003/02/05
		(liquid near crystal)) and (gate near line) and	US-PGPUB;	11:09
		(drain near line) and (tft or (thin near film	EPO; JPO;	
		near transistor)) and (pixel near electrode)	DERWENT;	
		and (counter near electrode))) and	IBM_TDB	
		(photoconductive or (photo near conductive)		
		or photoconduction or photoconductivity or		
		(photo near conduct) or (photo near		
		conductivity) or (photo near conduction))	HERAT	2002/02/05
	13	fazli and erdem	USPAT;	2003/02/05
			US-PGPUB;	11:09
			EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	1

-	6	(((substrat n ar10 transpar nt) and (lcd or	USPAT;	2003/02/05
	1	(liquid near crystal)) and (gat near line) and	US-PGPUB;	11:10
	i	(drain near lin ) and (tft or (thin n ar film	EPO; JPO;	İ
		n ar transistor)) and (pixel n ar el ctr d )	DERWENT;	
		and (c unter near el ctr de))) and	IBM_TDB	1
		(photoconductiv r (ph to n arc nductive)		
		or photoconduction or photoconductivity or		1
		(photo near conduct) or (photo near		
		conductivity) or (photo near conduction) or		
		photocon)		
•	44	(US-6218206-\$ or US-6034747-\$ or	USPAT;	2003/02/05
		US-5989945-\$ or US-5926161-\$ or	US-PGPUB	11:10
		US-5831707-\$ or US-5828430-\$ or		1
	1	US-5646756-\$ or US-5434433-\$ or		1
		US-5426313-\$ or US-5185601-\$ or		
		US-5151806-\$ or US-4759610-\$ or		
		US-6500702-\$ or US-6486934-\$ or		
		US-6452658-\$ or US-6449026-\$ or		
		US-6362032-\$ or US-6335148-\$ or		
		US-6323051-\$ or US-6319760-\$ or		
		US-6309903-\$ or US-6292241-\$ or		
		US-6226060-\$ or US-6219118-\$ or		
		US-6097452-\$ or US-6091467-\$).did. or		
		(US-5990987-\$ or US-5953084-\$ or		
		US-5818550-\$ or US-5734455-\$ or		
		US-6323918-\$ or US-5929958-\$ or	1.13	
		US-5914762-\$ or US-5798744-\$ or		
		US-5751381-\$ or US-6344885-\$ or		
		US-6255131-\$).did. or (US-20020100908-\$ or		
		US-20010052951-\$ or US-20010030717-\$ or		
		US-20010015440-\$ or US-20020113916-\$ or		
		US-20020074547-\$ or		
		US-20020033907-\$).did.		1

•	5	((US-6218206-\$ r US-6034747-\$ r	USPAT;	2003/02/05
		US-5989945-\$ or US-5926161-\$ or	US-PGPUB;	11:12
	1	US-5831707-\$ r US-5828430-\$ or	EPO; JPO;	!
		US-5646756-\$ or US-5434433-\$ or	DERWENT;	
	1	US-5426313-\$ or US-5185601-\$ or	IBM_TDB	
		US-5151806-\$ or US-4759610-\$ r	ĺ	
		US-6500702-\$ or US-6486934-\$ or	!	1
		US-6452658-\$ or US-6449026-\$ or	!	
		US-6362032-\$ or US-6335148-\$ or		
		US-6323051-\$ or US-6319760-\$ or		
		US-6309903-\$ or US-6292241-\$ or		
		US-6226060-\$ or US-6219118-\$ or		
		US-6097452-\$ or US-6091467-\$).did. or		
		(US-5990987-\$ or US-5953084-\$ or		1
		US-5818550-\$ or US-5734455-\$ or		
		US-6323918-\$ or US-5929958-\$ or		
		US-5914762-\$ or US-5798744-\$ or		
		US-5751381-\$ or US-6344885-\$ or		
		US-6255131-\$).did. or (US-20020100908-\$ or		
		US-20010052951-\$ or US-20010030717-\$ or		
		US-20010015440-\$ or US-20020113916-\$ or		Î
		US-20020074547-\$ or		
		US-20020033907-\$).did.) and		; 1
		(photoconductive or (photo near conductive)		
		or photoconduction or photoconductivity or		<b>f</b>
		(photo near conduct) or (photo near		
		conductivity) or (photo near conduction) or		
		photocon)		
	39012	(photoconductive or (photo near conductive)	USPAT;	2003/02/05
		or photoconduction or photoconductivity or	US-PGPUB:	11:14
		(photo near conduct) or (photo near	EPO; JPO;	
		conductivity) or (photo near conduction) or	DERWENT:	
		photocon).ti,ab,clm.	IBM_TDB	
	33053	((photoconductive or (photo near	USPAT;	2003/02/05
	00000	conductive) or photoconduction or	US-PGPUB;	11:14
		photoconductivity or (photo near conduct)	EPO; JPO;	
		or (photo near conductivity) or (photo near	DERWENT;	
		conduction) or photocon).ti,ab,clm.) and	IBM_TDB	
		(photoconductive or (photo near conductive)	.5111_100	
		or photoconductive or (photoconductivity or	• II	
		(photo near conduct) or (photo near		
		conductivity) or (photo near conduction) or		
		photocon).ab.		

•	1	(((ph t c nductiv or (photo near	USPAT;	2003/02/05
		conductive) r ph toconduction or	US-PGPUB;	11:16
	1	photoc nductivity r (photo near c nduct)	EPO; JPO;	
	1	or (phot n arc ndu tivity) r (photo n ar	DERWENT;	
	Ţ	condu ti n) or ph t c n).ti,ab,clm.) and	IBM_TDB	
	1	(phot c nductiv or (phot n ar conductiv )		
	1	or photoconduction or photoconductivity or	1	
		(photo near conduct) or (photo near	ļ	
		conductivity) or (photo near conduction) or	,	
	-	photocon).ab.) and (source and drain and		
		gate and counter and pixel and (tft or (thin		
		near film near transistor))).clm.		1
	8	(((photoconductive or (photo near	USPAT;	2003/02/05
		conductive) or photoconduction or	US-PGPUB;	11:17
	İ	photoconductivity or (photo near conduct)	EPO; JPO;	!
		or (photo near conductivity) or (photo near	DERWENT;	
		conduction) or photocon).ti,ab,clm.) and	IBM_TDB	
		(photoconductive or (photo near conductive)		
		or photoconduction or photoconductivity or		
		(photo near conduct) or (photo near		
		conductivity) or (photo near conduction) or		
	100	photocon).ab.) and (source and drain and		
		gate and counter and pixel and (tft or (thin		
		near film near transistor)))		
	13	((photoconductive or (photo near	USPAT;	2003/02/05
		conductive) or photoconduction or	US-PGPUB;	11:17
		photoconductivity or (photo near conduct)	EPO; JPO;	
		or (photo near conductivity) or (photo near	DERWENT;	
		conduction) or photocon).ti,ab,clm.) and	IBM_TDB	
	1	(source and drain and gate and counter and		
		pixel and (tft or (thin near film near		
		transistor)))		₹ 1

- 56	(US-6218206-\$ or US-6034747-\$ r	USPAT;	2003/02/05
	US-5989945-\$ or US-5926161-\$ r	US-PGPUB;	11:18
	US-5831707-\$ or US-5828430-\$ r	DERWENT	
	US-5646756-\$ r US-5434433-\$ r		1
	US-5426313-\$ r US-5185601-\$ or	İ	1
	US-5151806-\$ r US-4759610-\$ or		l
	US-6500702-\$ or US-6486934-\$ or	}	•
!	US-6452658-\$ or US-6449026-\$ or		L
	US-6362032-\$ or US-6335148-\$ or	<u> </u>	ŧ
	US-6323051-\$ or US-6319760-\$ or		
	US-6309903-\$ or US-6292241-\$ or		
	US-6226060-\$ or US-6219118-\$ or		
	US-6097452-\$ or US-6091467-\$).did. or		
	(US-5990987-\$ or US-5953084-\$ or		
	US-5818550-\$ or US-5734455-\$ or		
	US-6323918-\$ or US-5929958-\$ or		
	US-5914762-\$ or US-5798744-\$ or		
	US-5751381-\$ or US-6344885-\$ or	-	
	US-6255131-\$ or US-6340818-\$ or		
	US-6340812-\$ or US-5589961-\$ or		
	US-5455883-\$ or US-5151688-\$ or		
	US-6342700-\$ or US-5962856-\$ or		
	US-5949502-\$ or US-5258705-\$ or		<u> </u>
	US-4938567-\$).did. or (US-20020100908-\$ or		1
	US-20010052951-\$ or US-20010030717-\$ or		
	US-20010015440-\$ or US-20020113916-\$ or		1
	US-20020074547-\$ or		
	US-20020033907-\$).did. or (JP-09222597-\$		
	or US-20010052951-\$).did.		

•	46 ((US-6218206-\$ r US-6034747-\$ or	USPAT;	2003/02/05
	US-5989945-\$ r US-5926161-\$ r	US-PGPUB;	11:19
	US-5831707-\$ r US-5828430-\$ r	EPO; JPO;	†
	US-5646756-\$ r US-5434433-\$ r	DERWENT;	1
	US-5426313-\$ r US-5185601-\$ r	IBM_TDB	
	US-5151806-\$ r US-4759610-\$ or	-	ł
	US-6500702-\$ or US-6486934-\$ or	i	1
	US-6452658-\$ or US-6449026-\$ or	Ť	i .
	US-6362032-\$ or US-6335148-\$ or		
	US-6323051-\$ or US-6319760-\$ or		
	US-6309903-\$ or US-6292241-\$ or		1
	US-6226060-\$ or US-6219118-\$ or		
	US-6097452-\$ or US-6091467-\$).did. or		
	(US-5990987-\$ or US-5953084-\$ or		}
	US-5818550-\$ or US-5734455-\$ or		
	US-6323918-\$ or US-5929958-\$ or		
	US-5914762-\$ or US-5798744-\$ or	İ	
	US-5751381-\$ or US-6344885-\$ or		
	US-6255131-\$ or US-6340818-\$ or		
	US-6340812-\$ or US-5589961-\$ or		
	US-5455883-\$ or US-5151688-\$ or		
	US-6342700-\$ or US-5962856-\$ or		
	US-5949502-\$ or US-5258705-\$ or		
	US-4938567-\$).did. or (US-20020100908-\$	or ¦	i I
	US-20010052951-\$ or US-20010030717-\$ o	or	
	US-20010015440-\$ or US-20020113916-\$ o	or	
	US-20020074547-\$ or		
	US-20020033907-\$).did. or (JP-09222597-\$	<b>;</b>	1
	or US-20010052951-\$).did.) and (substrate	•	
	near10 transparent)		

22	(((US-6218206-\$ or US-6034747-\$ or	USPAT;	2003/02/05
1	US-5989945-\$ or US-5926161-\$ r	US-PGPUB;	11:20
1	US-5831707-\$ or US-5828430-\$ r	EPO; JP ;	!
1	US-5646756-\$ or US-5434433-\$ r	DERWENT;	!
i	US-5426313-\$ r US-5185601-\$ r	IBM_TDB	
	US-5151806-\$ r US-4759610-\$ r		l
İ	US-6500702-\$ or US-6486934-\$ or		
	US-6452658-\$ or US-6449026-\$ or		
	US-6362032-\$ or US-6335148-\$ or		!
1	US-6323051-\$ or US-6319760-\$ or		
!	US-6309903-\$ or US-6292241-\$ or		!
	US-6226060-\$ or US-6219118-\$ or		
	US-6097452-\$ or US-6091467-\$).did. or		ļ
	(US-5990987-\$ or US-5953084-\$ or		İ
	US-5818550-\$ or US-5734455-\$ or		i
	US-6323918-\$ or US-5929958-\$ or		
	US-5914762-\$ or US-5798744-\$ or		
	US-5751381-\$ or US-6344885-\$ or		
	US-6255131-\$ or US-6340818-\$ or		Ì
	US-6340812-\$ or US-5589961-\$ or		
ļ	US-5455883-\$ or US-5151688-\$ or		!
	US-6342700-\$ or US-5962856-\$ or		
	US-5949502-\$ or US-5258705-\$ or		
	US-4938567-\$).did. or (US-20020100908-\$ or		
İ	US-20010052951-\$ or US-20010030717-\$ or		
	US-20010015440-\$ or US-20020113916-\$ or		
	US-20020074547-\$ or		
	US-20020033907-\$).did. or (JP-09222597-\$		
	or US-20010052951-\$).did.) and (substrate		
	near10 transparent)) and (gate near line)		
	and (drain near line)		

	17	(((US-6218206-\$ r US-6034747-\$ or	USPAT;	2003/02/05
		US-5989945-\$ or US-5926161-\$ or	US-PGPUB;	11:21
		US-5831707-\$ or US-5828430-\$ or	EPO; JPO;	ļ
		US-5646756-\$ r US-5434433-\$ r	DERWENT;	
İ		US-5426313-\$ r US-5185601-\$ r	IBM_TDB	
		US-5151806-\$ r US-4759610-\$ r		
-		US-6500702-\$ or US-6486934-\$ or		
		US-6452658-\$ or US-6449026-\$ or		
İ		US-6362032-\$ or US-6335148-\$ or		
1		US-6323051-\$ or US-6319760-\$ or		1
		US-6309903-\$ or US-6292241-\$ or		
ļ		US-6226060-\$ or US-6219118-\$ or		į
		US-6097452-\$ or US-6091467-\$).did. or		l
		(US-5990987-\$ or US-5953084-\$ or	1	i
		US-5818550-\$ or US-5734455-\$ or		:
ļ.		US-6323918-\$ or US-5929958-\$ or		
		US-5914762-\$ or US-5798744-\$ or		
		US-5751381-\$ or US-6344885-\$ or		
		US-6255131-\$ or US-6340818-\$ or		
		US-6340812-\$ or US-5589961-\$ or		
		US-5455883-\$ or US-5151688-\$ or		1
		US-6342700-\$ or US-5962856-\$ or		
		US-5949502-\$ or US-5258705-\$ or		
		US-4938567-\$).did. or (US-20020100908-\$ or		
		US-20010052951-\$ or US-20010030717-\$ or		
		US-20010015440-\$ or US-20020113916-\$ or		
		US-20020074547-\$ or		1,0
		US-20020033907-\$).did. or (JP-09222597-\$		1
		or US-20010052951-\$).did.) and (substrate		1
		near10 transparent)) and (((gate near line)		
		and (drain near line)) same (tft or (thin near		
1		film near transistor)))		

-	17	((((US-6218206-\$ r US-6034747-\$ r	USPAT;	2003/02/05
		US-5989945-\$ r US-5926161-\$ r	US-PGPUB;	11:21
•		US-5831707-\$ r US-5828430-\$ r	EPO; JPO;	1
Ì		US-5646756-\$ or US-5434433-\$ r	DERWENT;	į.
		US-5426313-\$ r US-5185601-\$ or	IBM_TDB	•
•		US-5151806-\$ r US-4759610-\$ r	1	! <del> </del>
		US-6500702-\$ or US-6486934-\$ or		
		US-6452658-\$ or US-6449026-\$ or		•
		US-6362032-\$ or US-6335148-\$ or		
		US-6323051-\$ or US-6319760-\$ or		
		US-6309903-\$ or US-6292241-\$ or		
K		US-6226060-\$ or US-6219118-\$ or		
1		US-6097452-\$ or US-6091467-\$).did. or		
1		(US-5990987-\$ or US-5953084-\$ or	7	
		US-5818550-\$ or US-5734455-\$ or		
		US-6323918-\$ or US-5929958-\$ or		
		US-5914762-\$ or US-5798744-\$ or		
		US-5751381-\$ or US-6344885-\$ or		
		US-6255131-\$ or US-6340818-\$ or		
		US-6340812-\$ or US-5589961-\$ or		
		US-5455883-\$ or US-5151688-\$ or		
i		US-6342700-\$ or US-5962856-\$ or	1	
		US-5949502-\$ or US-5258705-\$ or		1
İ		US-4938567-\$).did. or (US-20020100908-\$ or		
		US-20010052951-\$ or US-20010030717-\$ or		
		US-20010015440-\$ or US-20020113916-\$ or		
		US-20020074547-\$ or		
		US-20020033907-\$).did. or (JP-09222597-\$		
		or US-20010052951-\$).did.) and (substrate	13   1   11	
1		near10 transparent)) and (((gate near line)	M	1
		and (drain near line)) same (tft or (thin near		
		film near transistor)))) and ((pixel near		
		electrode) same (tft or (thin near film near		
		transistor)))		İ

- 14	((((US-6218206-\$ r US-6034747-\$ or	USPAT;	2003/02/05
	US-5989945-\$ or US-5926161-\$ or	US-PGPUB;	11:22
	US-5831707-\$ r US-5828430-\$ or	EPO; JP ;	i
	US-5646756-\$ or US-5434433-\$ r	DERWENT;	
	US-5426313-\$ or US-5185601-\$ r	IBM_TDB	1
	US-5151806-\$ or US-4759610-\$ or		
1	US-6500702-\$ or US-6486934-\$ or		
i	US-6452658-\$ or US-6449026-\$ or		
	US-6362032-\$ or US-6335148-\$ or		i
	US-6323051-\$ or US-6319760-\$ or		! !
	US-6309903-\$ or US-6292241-\$ or		
	US-6226060-\$ or US-6219118-\$ or		
	US-6097452-\$ or US-6091467-\$).did. or		i
	(US-5990987-\$ or US-5953084-\$ or		!
	US-5818550-\$ or US-5734455-\$ or		
	US-6323918-\$ or US-5929958-\$ or		
	US-5914762-\$ or US-5798744-\$ or		
	US-5751381-\$ or US-6344885-\$ or		
i	US-6255131-\$ or US-6340818-\$ or		9 =
	US-6340812-\$ or US-5589961-\$ or		
	US-5455883-\$ or US-5151688-\$ or	1 (3	
	US-6342700-\$ or US-5962856-\$ or		
	US-5949502-\$ or US-5258705-\$ or		
	US-4938567-\$).did. or (US-20020100908-\$ or		
	US-20010052951-\$ or US-20010030717-\$ or		
	US-20010015440-\$ or US-20020113916-\$ or		
	US-20020074547-\$ or		
	US-20020033907-\$).did. or (JP-09222597-\$		
	or US-20010052951-\$).did.) and (substrate		
	near10 transparent)) and (((gate near line)		
	and (drain near line)) same (tft or (thin near		
	film near transistor)))) and ((pixel near		
	electrode) same (counter near electrode))		

	13	((((US-6218206-\$ r US-6034747-\$ r	USPAT;	2003/02/05
		US-5989945-\$ or US-5926161-\$ r	US-PGPUB;	11:24
į		US-5831707-\$ or US-5828430-\$ r	EPO; JP ;	
Į		US-5646756-\$ r US-5434433-\$ or	DERWENT;	!
		US-5426313-\$ or US-5185601-\$ r	IBM_TDB	
-		US-5151806-\$ or US-4759610-\$ or		
1		US-6500702-\$ or US-6486934-\$ or		
		US-6452658-\$ or US-6449026-\$ or		
		US-6362032-\$ or US-6335148-\$ or		
		US-6323051-\$ or US-6319760-\$ or		
		US-6309903-\$ or US-6292241-\$ or		
100		US-6226060-\$ or US-6219118-\$ or		
		US-6097452-\$ or US-6091467-\$).did. or		
		(US-5990987-\$ or US-5953084-\$ or		İ
		US-5818550-\$ or US-5734455-\$ or		
		US-6323918-\$ or US-5929958-\$ or		
l		US-5914762-\$ or US-5798744-\$ or		
		US-5751381-\$ or US-6344885-\$ or		1
		US-6255131-\$ or US-6340818-\$ or		
		US-6340812-\$ or US-5589961-\$ or		
		US-5455883-\$ or US-5151688-\$ or		
		US-6342700-\$ or US-5962856-\$ or		
		US-5949502-\$ or US-5258705-\$ or	]	
		US-4938567-\$).did. or (US-20020100908-\$ or		
		US-20010052951-\$ or US-20010030717-\$ or		
		US-20010015440-\$ or US-20020113916-\$ or		
		US-20020074547-\$ or		
		US-20020033907-\$).did. or (JP-09222597-\$		
		or US-20010052951-\$).did.) and (substrate		
	Ì	near10 transparent)) and (((gate near line)		
		and (drain near line)) same (tft or (thin near		
		film near transistor)))) and ((pixel near		
		electrode) same (counter near electrode)))		
		and ((source near electrode) same (tft or		
		(thin near film near electrode)))		